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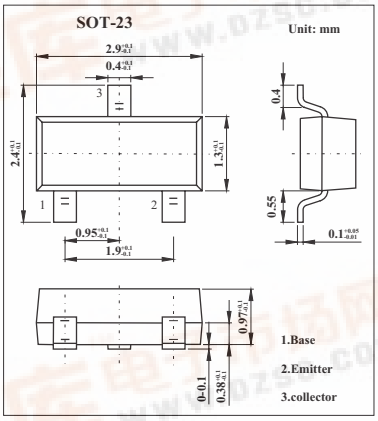
General Purpose Transistor

2SD2226K



Features

- High DC current gain.
- High emitter-base voltage.
- Low saturation voltage.

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	60	V
Collector-emitter voltage	V_{CEO}	50	V
Emitter-base voltage	V_{EBO}	12	V
Collector current	I_C	0.15	A
		0.2 *	
Collector power dissipation	P_C	0.2	W
Junction temperature	Tj	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

* Single pulse Pw=100ms.

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	BV_{CBO}	I_C=10μA	60			V
Collector-emitter breakdown voltage	BV_{CEO}	I_C=1mA	50			V
Emitter-base breakdown voltage	BV_{EBO}	I_E=10μA	12			V
Collector cutoff current	I_{CBO}	V_{CB}=50V			0.3	μA
Emitter cutoff current	I_{EBO}	V_{EB}=12V			0.3	μA
Collector-emitter saturation voltage *	$V_{CE(sat)}$	I_C/I_B=50mA/5mA			0.3	V
DC current transfer ratio *	h_{FE}	V_{CE}=5V, I_C=1mA	820		2700	
Output capacitance *	f_T	V_{CE}=5V, I_E= -10mA, f=100MHz		250		MHz
Transition frequency	Cob	V_{CB}=5V, I_E=0, f=1MHz		3.5		pF

* Measured using pulse current.

h_{FE} Classification

Marking	BJ	
Rank	V	W
h_{FE}	820～1800	1200～2700

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